

ELECTRICAL SPECIFICATIONS		
6.000MHz		
±50ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range,Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)		
±5ppm/year Maximum		
-40°C to +85°C		
5.0Vdc ±10%		
45mA Maximum (Unloaded)		
Vdd-0.4Vdc Minimum (IOH = -16mA)		
0.4Vdc Maximum (IOL = +16mA)		
4nSec Maximum (Measured at 20% to 80% of waveform)		
50 ±10(%) (Measured at 1.4Vdc with TTL Load or 50% of waveform with HCMOS Load)		
50pF HCMOS Load Maximum		
CMOS		
Tri-State (Disabled Output: High Impedance)		
+2.0Vdc Minimum to enable output, +0.8Vdc Maximum to disable output, No Connect to enable output.		
50μA Maximum (Pin 1 = Ground)		
30mA Maximum (Pin 1 = Ground)		
250pSec Maximum, ±100pSec Typical		
±50pSec Maximum		
10mSec Maximum		
-55°C to +125°C		

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS			
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V		
Fine Leak Test	MIL-STD-883, Method 1014, Condition A		
Flammability	UL94-V0		
Gross Leak Test	MIL-STD-883, Method 1014, Condition C		
Mechanical Shock	MIL-STD-883, Method 2002, Condition B		
Moisture Resistance	MIL-STD-883, Method 1004		
Moisture Sensitivity	J-STD-020, MSL 1		
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K		
Resistance to Solvents	MIL-STD-202, Method 215		
Solderability	MIL-STD-883, Method 2003		
Temperature Cycling	MIL-STD-883, Method 1010, Condition B		
Vibration	MIL-STD-883, Method 2007, Condition A		



MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State (High Impedance)
2	Ground/Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	6.000M
3	PXXYZZ P=Configuration Designatol XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1



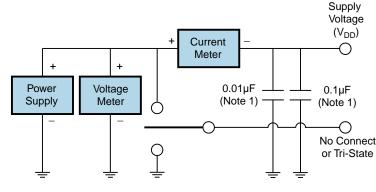
OUTPUT WAVEFORM & TIMING DIAGRAM

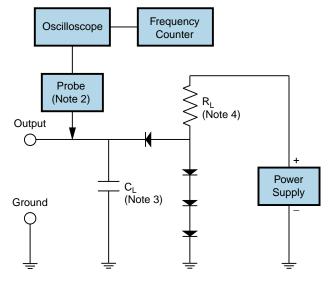


Test Circuit for TTL Output

Output Load Drive Capability	R _L Value (Ohms)	C _L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability





Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

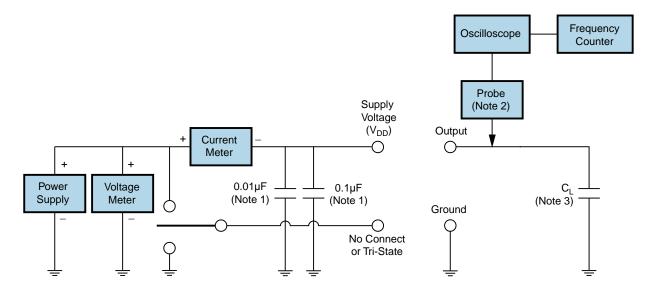
Note 3: Capacitance value C_{L} includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



Test Circuit for CMOS Output



Note 1: An external $0.1\mu F$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu F$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

<u> </u>	
T _s MAX to T _∟ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _S MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _S MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _S TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)